

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







NPN High-Power Transistors

Designed for general-purpose power amplifier and switching applications.

Features

- ESD Ratings: Machine Model, C; > 400 V Human Body Model, 3B; > 8000 V
- Epoxy Meets UL 94 V-0 @ 0.125 in
- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	TIP33A TIP33C	V _{CEO}	60 100	Vdc
Collector - Base Voltage	TIP33A TIP33C	V _{CBO}	60 100	Vdc
Emitter – Base Voltage		V _{EBO}	5.0	Vdc
Collector Current - Continuous - Peak (Note 1)		I _C	10 15	Adc Apk
Base Current - Continuous		I _B	3.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	80 0.64	Watts W/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	−65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.56	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	35.7	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



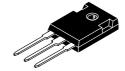
ON Semiconductor®

http://onsemi.com

10 AMPERE NPN SILICON POWER TRANSISTORS 60 & 100 VOLT, 80 WATTS



SOT-93 (TO-218) CASE 340D STYLE 1



TO-247 CASE 340L STYLE 3

NOTE: Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

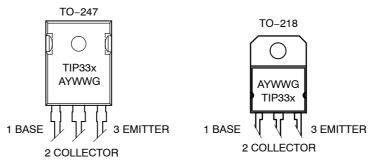
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAMS



TIP33x = Device Code A = Assembly Location

 A
 = Assembly Location

 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

ORDERING INFORMATION

Device Order Number	Package Type	Shipping
TIP33AG	TO-218 (Pb-Free)	30 Units / Rail
TIP33CG	TO-218 (Pb-Free)	30 Units / Rail
TIP33AG	TO-247 (Pb-Free)	30 Units / Rail
TIP33CG	TO-247 (Pb-Free)	30 Units / Rail

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 30 \text{ mA}, I_B = 0)$	TIP33A TIP33C	V _{CEO(sus)}	60 100	_ _	Vdc
Collector–Emitter Cutoff Current $(V_{CE} = 30 \text{ V}, I_B = 0)$ $(V_{CE} = 60 \text{ V}, I_B = 0)$	TIP33A TIP33C	I _{CEO}	-	0.7	mA
Collector–Emitter Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{EB} = 0)$		I _{CES}	-	0.4	mA
Emitter-Base Cutoff Current (V _{EB} = 5.0 V, I _C = 0)		I _{EBO}	-	1.0	mA
ON CHARACTERISTICS (Note 2)			•	•	•
DC Current Gain $(I_C = 1.0 \text{ A, V}_{CE} = 4.0 \text{ V})$ $(I_C = 3.0 \text{ A, V}_{CE} = 4.0 \text{ V})$		h _{FE}	40 20	_ 100	-
Collector–Emitter Saturation Voltage ($I_C = 3.0 \text{ A}, I_B = 0.3 \text{ A}$) ($I_C = 10 \text{ A}, I_B = 2.5 \text{ A}$)		V _{CE(sat)}	- -	1.0 4.0	Vdc
Base-Emitter On Voltage ($I_C = 3.0 \text{ A}, V_{CE} = 4.0 \text{ V}$) ($I_C = 10 \text{ A}, V_{CE} = 4.0 \text{ V}$)		V _{BE(on)}	_ _	1.6 3.0	Vdc
DYNAMIC CHARACTERISTICS			•	•	•
Small–Signal Current Gain ($I_C = 0.5 \text{ A}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$)		h _{fe}	20	_	-
Current-Gain — Bandwidth Product (I _C = 0.5 A, V _{CE} = 10 V, f = 1.0 MHz)		f _T	3.0	_	MHz

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

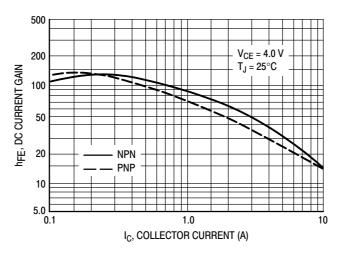


Figure 1. DC Current Gain

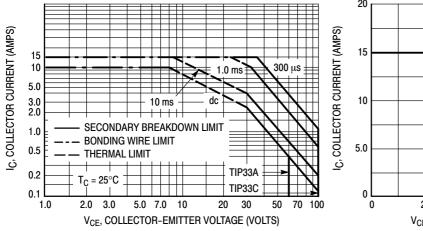


Figure 2. Maximum Rated Forward Bias Safe Operating Area

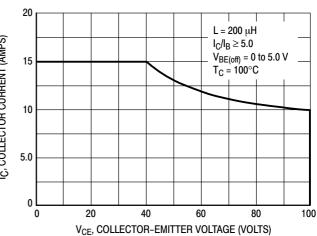


Figure 3. Maximum Rated Forward Bias Safe Operating Area

FORWARD BIAS

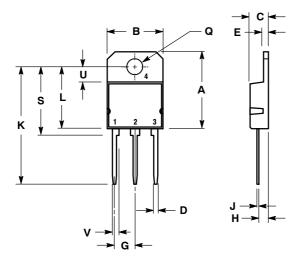
The Forward Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during forward bias. The data is based on T_C = $25\,^{\circ}$ C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10%, and must be derated thermally for T_C > $25\,^{\circ}$ C.

REVERSE BIAS

The Reverse Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during reverse biased turn-off. This rating is verified under clamped conditions so the device is never subjected to an avalanche mode.

PACKAGE DIMENSIONS

SOT-93 (TO-218) CASE 340D-02 **ISSUE E**



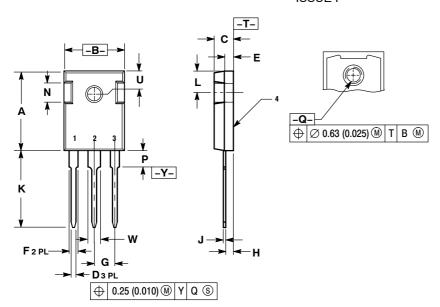
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α		20.35		0.801	
В	14.70	15.20	0.579	0.598	
С	4.70	4.90	0.185	0.193	
D	1.10	1.30	0.043	0.051	
Е	1.17	1.37	0.046	0.054	
G	5.40	5.55	0.213	0.219	
Н	2.00	3.00	0.079	0.118	
J	0.50	0.78	0.020	0.031	
K	31.00	31.00 REF		1.220 REF	
L		16.20		0.638	
Q	4.00	4.10	0.158	0.161	
S	17.80	18.20	0.701	0.717	
U	4.00 REF		0.157	REF	
V	1.75 REF		0.0)69	

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

 - COLLECTOR

TO-247 CASE 340L-02 ISSUE F



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	20.32	21.08	0.800	8.30
В	15.75	16.26	0.620	0.640
С	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
Ε	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
Н	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P		4.50		0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242	BSC
W	2.87	3.12	0.113	0.123

- STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative